



Electronic Properties of AgBiS₂ Nanocrystal Structure Variations

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Abstract. Today, most of the nanocrystals researched for use in electronic devices, such as solar cells and photodetectors, worldwide include toxic metal elements (Pb, Cd, or Hg) or scarce elements. To replace them with eco-friendly compounds, it is necessary to understand their electronic and optical properties to support their high performance. AgBiS₂, a promising ternary compound for environmental applications, is expected to be utilized in realizing solution-processed solar cells with high performance in terms of conversion efficiency. Same as PbS, AgBiS₂ has a NaCl-type cubic structure, but with two different cations (Ag or Bi). The order of these ions makes a difference in their structural and electronic properties. However, it is challenging to measure the details of the cation order experimentally. Therefore, a computational approach is crucial for investigating nanoscale properties. Here, we performed first-principles calculations using density functional theory (DFT) for one of the AgBiS₂ bulk crystalline structure phases, with a body-centered tetragonal (*bct*) primitive cell, and compared the results with those of the reported synthesized AgBiS₂ bulk crystal. The computed lattice constants are in close agreement with the experimental value. However, the electronic band structure has a small direct band gap of 0.07 eV, as determined by the PBE functional. In comparison with other phases, it is evident that cation order significantly affects the electronic properties.

Keywords: Nanocrystals, AgBiS₂, electronic band structure, DFT calculation.

1 Introduction

Nowadays, the performance of electronic devices has been increasing significantly due to ongoing research on materials and devices worldwide, which aims to address humanity's demands, including energy problems. For example, it is expected that solar cells incorporating nanomaterials, such as quantum dots, will exhibit good performance, surpassing the state-of-the-art silicon technologies. As of 2024, a solar cell with organic cation perovskite-based quantum dots has demonstrated a power conversion efficiency of 18.1% [1]. However, there are still many unoptimized uses of the unique features of the quantum dots. Quantum dots enable us to tune the band gap value by changing their size. The quantum confinement effect is responsible for this

feature. The full utilization of these features to demonstrate high-performance solar cells is currently underway. However, most of the researched nanocrystals for these applications contain toxic metal elements, such as Pb, Cd, or Hg. Furthermore, Se and Te, which are mainstream for studying metal chalcogenide nanocrystals, are scarce on Earth and challenging to find. Therefore, we need to find better alternatives than these nanocrystal compounds.

The ternary compound AgBiS₂ is a promising material for eco-friendly optoelectronic devices, including solar cells. [2] According to experimental reports, the band gap of this compound is approximately 0.9 eV in its bulk crystal form. [3] If the quantum confinement effect can be strongly controlled in the nanocrystal form of this compound, the band gap value can be enlarged. However, due to the present challenge of size limitation, the obtained band gap of AgBiS₂ nanocrystals can only be enlarged up to 1.1 – 1.3 eV, which is not significantly different from its bulk value. [2][4][5][6][7] Nevertheless, these bandgap values are within the ideal wavelength range for solar cell operation, comparable to those of silicon and PbS quantum dots.

There are two types of AgBiS₂: schapbachite and matildite. Recently, we synthesized AgBiS₂ nanocrystals that exhibited semiconducting behavior and were confirmed to be schapbachite AgBiS₂. [8] Same as cubic PbS, schapbachite AgBiS₂ has a NaCl-like cubic structure and space group $Fm\bar{3}m$ with two cations (Ag and Bi) and one anion (S). Therefore, there are many possibilities of crystalline structure depending on the cation order. On the other hand, matildite AgBiS₂ has a trigonal structure and space group $P\bar{3}m1$. [9] Two of the possible crystalline structures with VESTA [10] are shown in Fig. 1(a-b). Bulk AgBiS₂ crystallizes in a trigonal structure at room temperature and transforms to a cation-disordered cubic structure. [11]

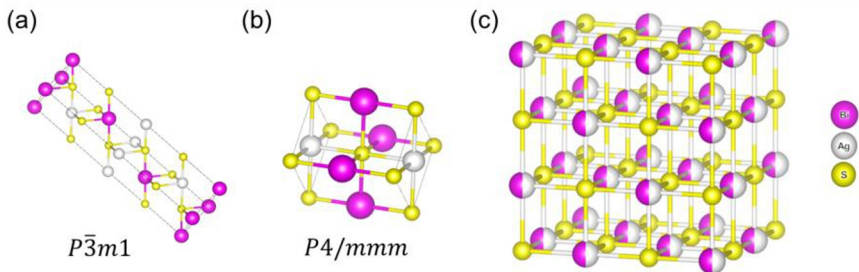


Fig. 1. Two of the variations of AgBiS₂ primitive cells: (a) trigonal $P\bar{3}m1$, and (b) tetragonal $P4/mmm$. (c) The cubic supercell includes 64 atoms

Although the cation order influences the structural and electronic properties, it is difficult to investigate the cation order experimentally. Therefore, computational calculations are crucial in explaining the cation order, which can serve as a guideline for designing related experiments.

There have been reports on the theoretical calculation study of AgBiS₂, and many of them have departed from various possible crystalline structures. For instance, some reports indicated that AgBiS₂ with a tetragonal structure (space group: $P4/mmm$) has no band gap, [12][13][14] suggesting this compound is not a semiconductor. On the

other hand, Mehdaoui et al. [15] indicated that AgBiS_2 with $P\bar{3}m1$ structure has less total energy than AgBiS_2 with $P4/mmm$ structure, suggesting that the $P\bar{3}m1$ structure is more stable. Other researchers have attempted to calculate variations in other crystal structures. [12][16][17] It was reported that ion order might be important. Some calculations revealed that the Ag-S-Ag-S chain contributes to the valence band maximum, and the Bi-S-Bi-S chain contributes to the conduction band minimum. [12] Considering cation disorder, cubic unit supercells are usually used for calculations, as shown in Fig. 1(c). The supercell in Fig. 1(c) contains 32 S, 16 Ag, and Bi atoms as an example. Even in this case, the number of combinations of Ag and Bi is $32!/(16!)^2$ without considering symmetry. [13]

The prospect of this compound demonstrating a solar cell with high power conversion efficiency has been conceptually predicted, suggesting that an ultra-thin film of AgBiS_2 may achieve a high-power conversion efficiency (PCE) of 25%. [18] However, to date, the reported efficiency of AgBiS_2 thin-film solar cells is still around 9-10%. Therefore, to fabricate ideal solar cells, it is necessary to understand the optical and electronic properties, especially the intrinsic properties of the materials.

Here, we report the results of a computational study on the electronic properties of the AgBiS_2 crystal structure with body-centered tetragonal (*bct*) structure (space group $I4_1/amd$). Although $I4_1/amd$ AgBiS_2 has less total energy than $P4/mmm$ AgBiS_2 theoretically, there are less researches for $I4_1/amd$ AgBiS_2 than $P4/mmm$ AgBiS_2 . [16] In this study, we performed first-principles calculations to investigate the electronic band structures of AgBiS_2 using two kinds of approximations. Understanding the electronic band structures of this compound will enable us to predict whether variations in its structure will lead to the formation of metal, semiconductor, or insulator behaviors (Fig. 2). [19]

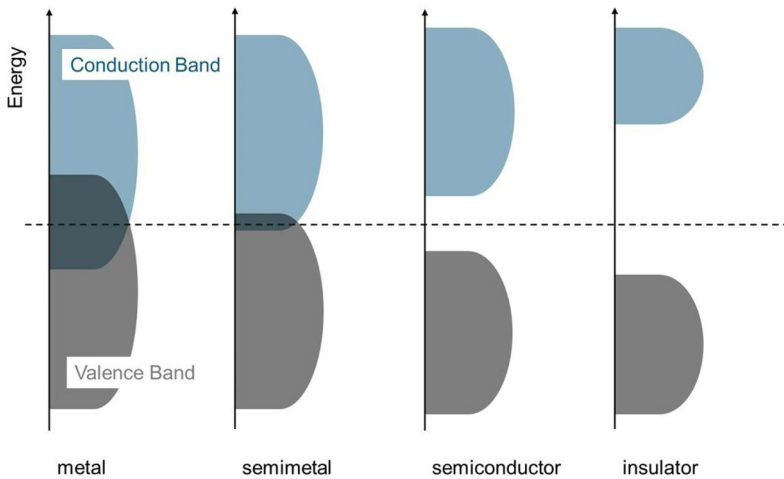


Fig. 2. The illustration of the electronic band diagram for each type of material: metal, semimetal, semiconductor, and insulator. [19]

Metallic materials have their Fermi level in the conduction band, resulting in a high density of free electrons, and their conduction band and valence band overlap in many cases. In contrast, semiconductors and insulators exhibit areas where there are no allowed electronic energy states between their conduction bands and valence bands, which is manifested as the electronic band gap.

2 Materials and Methods

2.1 Materials

In this study, we focus on one of the schapbachite AgBiS₂ crystalline structure phases: body-centered tetragonal (*bct*) structure with space group $I4_1/amd$. The primitive cell is shown in Fig. 3. This phase was introduced by Ju et al. [12] as the AF-III primitive cell. For the calculation performed in this study, the unit cell used is a tetragonal structure, serving as an approximation to the *bct* structure.

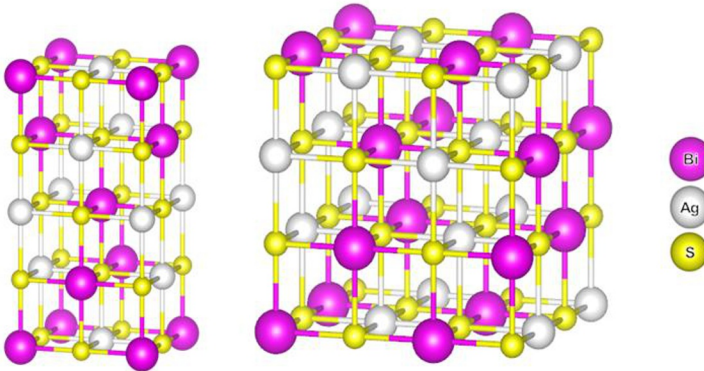


Fig. 3. (left)The primitive cell and (right)the supercell (with 64 atoms) of AgBiS₂ $I4_1/amd$ structure.

2.2 Methods

First-principles calculations were performed using Density Functional Theory (DFT) within the Quantum ESPRESSO [20][21][22] package. In this study, a full-relativistic pseudopotential is used in conjunction with the PBE [23] and LDA [24] exchange–correlation (*xc*) functionals. PBE is one of the generalized gradient approximation (GGA) forms [25]. LDA is the simplest approximation form for the *xc* functional that considers the electron density. GGA introduces a dependence on the electron density gradient. All calculations were performed using an energy cutoff of 45.0 Ry. For electron–electron interaction, the projected augmented wave (PAW) method [26][27] is used.

3 Results

The appropriate lattice constants of AgBiS_2 were investigated. The computed lattice constants are shown in Table 1. The lattice constant a in the primitive cell is compatible with that in the cubic structure, and these are similar to twice the length of the Ag-S or Bi-S chains. The computed values with the PBE functional are in good agreement with a reference journal,[16] where all-electron calculations with the PBE functional were carried out. The experimental lattice constants for the cubic structure (with cation order not identified) were obtained at 5.651 Å from references for comparison. [28] [29]

Table 1. The computed lattice parameters.

Parameter	PBE	LDA	Ref. (PBE) [16]	Expt. [28] [29]
Lattice constant a [Å]	5.637	5.516	5.70	5.651
Lattice constant c [Å]	11.44	10.88	11.45	–
c/a	2.030	1.972	2.01	–
Unit cell volume V [Å ³]	363.7	330.9	372.0	–

To understand the electronic properties of bulk AgBiS_2 , we performed the band calculations. The electronic band structures for bulk AgBiS_2 with $I4_1/amd$ structure at the PBE and LDA levels are shown in Fig. 4. The horizontal axis represents the high symmetry k-points in the Brillouin zone. [30]

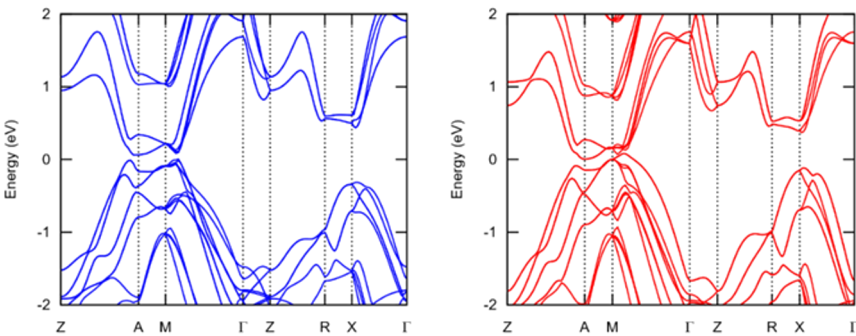


Fig. 4. The electronic band structures at the (left) PBE and (right) LDA level.

For the band structure with the PBE functional, a small direct band gap of 0.07 eV is obtained. This band gap value is close to the reference value (0.05 eV). [16] On the other hand, there is no band gap in the band structure obtained from the calculation using the LDA functional.

4 Discussion

Although the band structure exhibits a band gap with the PBE functional (0.07 eV), this value is significantly smaller than the experimental result (0.9 eV). [8] From this difference, it is suggested that $I4_1/amd$ structure phase is not the experimentally synthesized AgBiS₂.

For other structure phases, matildite AgBiS₂ ($P\bar{3}m1$) has an indirect band gap of 0.42 eV within the PBE functional.[14] Also, as mentioned above, $P4/mmm$ structure phase has no band gap [12][13][14]. One thing to consider is that LDA and GGA tend to underestimate the band gap value generally.

Experimentally, the reported band gap values of AgBiS₂ are various. This band gap difference may be dependent not only on nanocrystal sizes, but also on the cation order. For example, AgBiS₂ quantum dots synthesized by two groups have a band gap of 1.10 eV for 4.2 nm size [6] and of 1.3 eV for 4.62 ± 0.97 nm size [2]. These crystals were synthesized using various methods [31], resulting in different cation orders, crystal shapes, and so on.

5 Conclusion

We have performed the computational study for AgBiS₂ bulk with $I4_1/amd$ structure phase. The electronic band structure has a band gap of 0.07 eV for the PBE level and no band gap for the LDA level. This value is far smaller than the experimentally obtained band gap of 0.9 eV. Furthermore, according to reports from other researchers, other cation order phases have different band gap values theoretically. These results indicate that cation order has a strong influence on electronic properties. Controlling the cation order is crucial for making AgBiS₂ nanocrystals into a building block for solar cells with improved performance and other optoelectronic and energy device applications.

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Disclosure of Interests. The authors declare no conflicts of interest.

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